



n-channel transducer/microphone preamplifiers designed for . . .

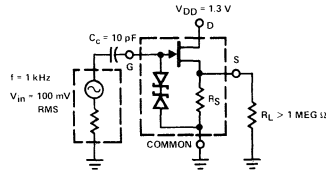
Performance Curves
NYFA NYFC See Section 4

- Hearing Aid Input Stages
- High Impedance Transducer Buffer Amplifiers
 - Electret-Condenser
 - Ceramic
 - Piezo-Electric
 - Capacitive
 - Air Condenser
- Self-Biased General Purpose High Impedance Source Followers

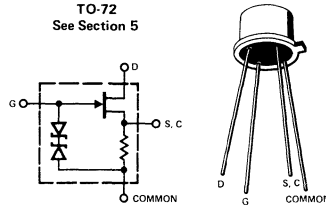
BENEFITS

- Complete Preamplifier, Requires No External Components
- Compact for Placement at Transducer
- Operates on Single Battery
- Ultra-High Input Impedance
5 x 10⁹ Ω Typical
- Available in Chip Form for Hybrid Systems

TEST CONFIGURATION



TO-72
See Section 5



ABSOLUTE MAXIMUM RATINGS (25°C)

Drain-Source and Drain-Gate Voltage	30 V
Gate Voltage (With Respect to Common)	±2.0 V
Forward Gate Current	1 mA
Total Device Dissipation (25°C Free-Air)	180 mW
Linear Derating Factor (to 85°C)	3.0 mW/°C
Storage Temperature Range	-55 to +150°C
Operating Temperature Range	-25 to +85°C
Lead Temperature (1/16" from Case for 10 Sec.)	260°C

ELECTRICAL CHARACTERISTICS (25°C unless otherwise noted)

Characteristic	T100			T300			Unit	TEST CONDITIONS All characteristics (unless otherwise specified) are measured in Test Configuration with V _{IN} = 100 mV (RMS), f = 1 kHz, C _C = 10 pF, V _{DD} = 1.3 V, R _L > 1 MEG Ω
	Min	Typ	Max	Min	Typ	Max		
1 S T I R I C A M I C BV _{DSS} Drain-Source (Drain-Gate) Breakdown ¹	30			30			V	I _D = 1 μA, V _{IN} = 0, C _C Shorted
2 I _D Operating Drain Current Range	10		50	70		350	μA	V _{IN} = 0, C _C Shorted
3 R _{in} Input Resistance ²	200M	5G		200M	5G		Ω	V _{IN} = 100 mV DC Measurement, C _C Shorted
4 R _{out} Output Resistance	1500		3500	500		1300	Ω	V _{IN} = 0, C _C Shorted
5 A _v Voltage Gain	0.40	0.60		0.30	0.45		V/V	
6 THD Total Harmonic Distortion		1.0			1.0		%	
7 e _{out} Broadband Output Noise Voltage			4.0			2.0	μV	V _{IN} = 0, f = 10 Hz to 10 kHz, C _C Shorted
8 C _{in} Input Capacitance	3.0	4.0		3.0	4.0		pF	V _{DD} = 20 V, V _{IN} = 0
9 C _{out} Output Capacitance	4.4	6.0		4.4	6.0		pF	f = 1 MHz, C _C Shorted

NYFC NYFA

NOTES:

1. Drain-Gate Breakdown Guaranteed by Drain-Source Breakdown Test. 2. M = 10⁶, G = 10⁹.



APPLICATIONS

Basic JFET Source Follower Equations are:

$$I_D = I_{DSS} \left(1 - \frac{V_{GS}}{V_P}\right)^2 \quad (1)$$

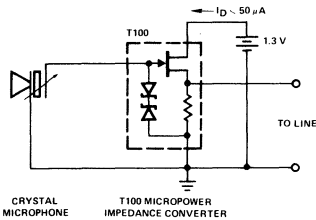
$$R_{OUT} = \frac{R_S}{1 + g_{fs} R_S} \quad (4)$$

where $V_{GS} = -I_D R_S \quad (2)$

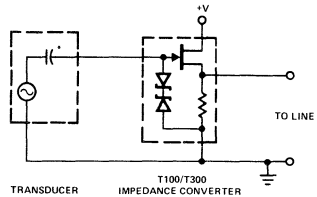
$$A_V = g_{fs} R_{OUT} \quad (5)$$

$$g_{fs} = \frac{-2 I_{DSS}}{V_P} \left(\frac{I_D}{I_{DSS}}\right)^{\frac{1}{2}} \quad (3)$$

T100 as a Micropower Preampifier –
As in a Hearing Aid Input

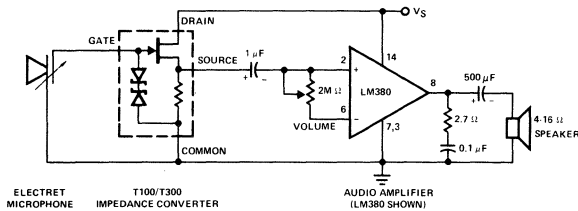


T100/T300 as an Impedance Converter
for Transducer Input

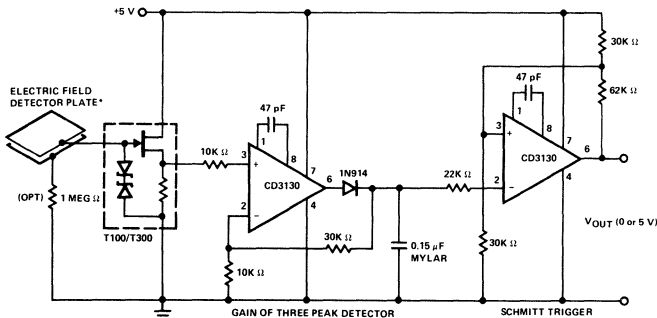


*NO CAPACITOR ISOLATION IS REQUIRED FOR CAPACITIVE TRANSDUCERS OR HIGH-IMPEDANCE PURE VOLTAGE SOURCES.

T100/T300 as a Preampifier in a Microphone Amplifier Circuit



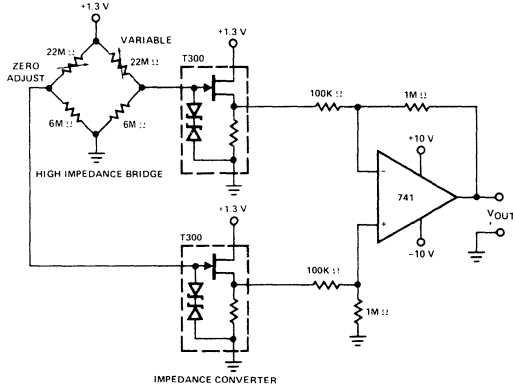
T100/T300 as a Self-Biased Proximity Sensor Works on Detected Changing Field



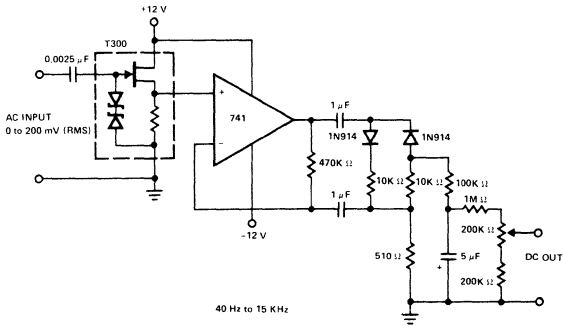
*DETECTOR PLATE MAY BE DOUBLE-SIDED PC BOARD OR ANY INSULATED METAL SHEET

APPLICATIONS (Cont'd)

T300's as Low Signal Level, High Impedance Instrumentation Amplifier



T100 in a High Impedance Precision Rectifier for AC/DC Converter



Source Follower with Voltage Gain Typically Greater Than 0.95 V/V and Z_{OUT} Typically Less Than 60Ω

